Product data sheet

1. Product profile

1.1 General description

NPN silicon microwave transistor for high speed, low noise applications in a plastic, 4-pin dual-emitter SOT343F package.

1.2 Features and benefits

- Low noise high linearity microwave transistor
- High output third-order intercept point 34 dBm at 1.8 GHz
- 40 GHz f_T silicon technology

1.3 Applications

- Ka band oscillators DRO's
- C-band high output buffer amplifier
- ZigBee
- LTE, cellular, UMTS

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-	16	V
V_{CEO}	collector-emitter voltage	open base	-	-	5.5	V
V_{EBO}	emitter-base voltage	open collector	-	-	2.5	V
I _C	collector current		-	70	100	mA
P _{tot}	total power dissipation	$T_{sp} \le 85 ^{\circ}C$	-	-	490	mW
h _{FE}	DC current gain	I_C = 20 mA; V_{CE} = 2 V; T_j = 25 °C	90	135	180	
C _{CBS}	collector-base capacitance	V _{CB} = 2 V; f = 1 MHz	-	404	-	fF
f⊤	transition frequency	$I_C = 60$ mA; $V_{CE} = 1$ V; $f = 2$ GHz; $T_{amb} = 25$ °C	-	18	-	GHz
$G_{p(max)}$	maximum power gain	$I_C = 60 \text{ mA}; V_{CE} = 1 \text{ V}; f = 1.8 \text{ GHz};$ $T_{amb} = 25 \text{ °C}$	-	20.5	-	dB
NF	noise figure	I_C = 15 mA; V_{CE} = 2 V; f = 1.8 GHz; Γ_S = Γ_{opt}	-	0.65	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	I_C = 70 mA; V_{CE} = 4 V; Z_S = Z_L = 50 Ω ; f = 1.8 GHz; T_{amb} = 25 °C	-	22	-	dBm

^[1] T_{sp} is the temperature at the solder point of the emitter lead.

 $[\]label{eq:Gpmax} \mbox{[2]} \quad \mbox{$G_{p(max)}$ is the maximum power gain, if $K > 1$. If $K < 1$ then $G_{p(max)}$ = Maximum Stable Gain (MSG).}$



2. Pinning information

Table 2. Discrete pinning

Pin	Description	Simplified outline	Graphic symbol
1	emitter		
2	base	3 4	4
3	emitter		2 —
4	collector		.)
			1, 3
		2 1	mbb159

3. Ordering information

Table 3. Ordering information

Type number	r Package			
	Name	Description	Version	
BFU690F	-	plastic surface-mounted flat pack package; reverse pinning; 4 leads	SOT343F	

4. Marking

Table 4. Marking

Type number	Marking	Description
BFU690F	D4*	* = p : made in Hong Kong
		* = t : made in Malaysia
		* = w : made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	16	V
V_{CEO}	collector-emitter voltage	open base	-	5.5	V
V_{EBO}	emitter-base voltage	open collector	-	2.5	V
I _C	collector current		-	100	mA
P _{tot}	total power dissipation	$T_{sp} \le 85 ^{\circ}C$ [1]	-	490	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

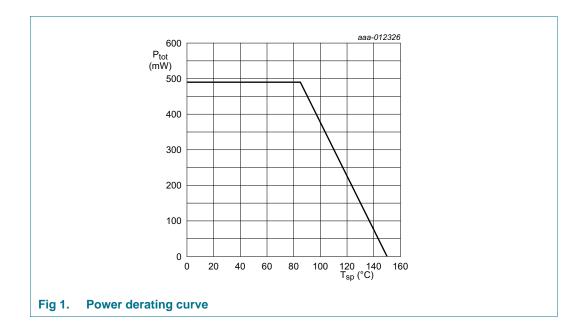
^[1] T_{sp} is the temperature at the solder point of the emitter lead.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	<u>[1]</u>	132	K/W

[1] Determined by simulation.



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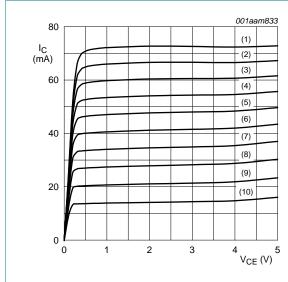
7. Characteristics

Table 7. Characteristics

 $T_j = 25$ °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 2.5 \mu A; I_E = 0 \text{ mA}$	16	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 1 mA; I _B = 0 mA	5.5	-	-	V
I _C	collector current		-	70	100	mΑ
I _{CBO}	collector-base cut-off current	I _E = 0 mA; V _{CB} = 8 V	-	-	100	nΑ
h _{FE}	DC current gain	I _C = 20 mA; V _{CE} = 2 V	90	135	180	
C _{CES}	collector-emitter capacitance	V _{CB} = 2 V; f = 1 MHz	-	527	-	fF
C _{EBS}	emitter-base capacitance	V _{EB} = 0.5 V; f = 1 MHz	-	1699	-	fF
C _{CBS}	collector-base capacitance	V _{CB} = 2 V; f = 1 MHz	-	404	-	fF
f _T	transition frequency	I_C = 60 mA; V_{CE} = 1 V; f = 2 GHz; T_{amb} = 25 °C	-	18	-	GHz
G _{p(max)}	maximum power gain	$I_C = 60 \text{ mA}; V_{CE} = 1 \text{ V}; T_{amb} = 25 \text{ °C}$ [1]				
		f = 1.5 GHz	-	22	-	dB
		f = 1.8 GHz	-	20.5	-	dB
		f = 2.4 GHz	-	17	-	dB
S ₂₁ ²	insertion power gain	$I_C = 60 \text{ mA}; V_{CE} = 1 \text{ V}; T_{amb} = 25 \text{ °C}$				
		f = 1.5 GHz	-	15	-	dB
		f = 1.8 GHz	-	13.5	-	dB
		f = 2.4 GHz	-	11	-	dB
NF	noise figure	I_C = 15 mA; V_{CE} = 2 V; Γ_S = Γ_{opt} ; Γ_{amb} = 25 °C				
		f = 1.5 GHz	-	0.60	-	dB
		f = 1.8 GHz	-	0.65	-	dB
		f = 2.4 GHz	-	0.70	-	dB
G _{ass}	associated gain	I_C = 15 mA; V_{CE} = 2 V; Γ_S = Γ_{opt} ; T_{amb} = 25 °C				
		f = 1.5 GHz	-	18.5	-	dB
		f = 1.8 GHz	-	17.5	-	dB
		f = 2.4 GHz	-	15.5	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	I_C = 70 mA; V_{CE} = 4 V; Z_S = Z_L = 50 Ω ; T_{amb} = 25 °C				
		f = 1.5 GHz	-	22	-	dBm
		f = 1.8 GHz	-	22	-	dBm
		f = 2.4 GHz	-	20	-	dBm
IP3	third-order intercept point	I_C = 70 mA; V_{CE} = 4 V; Z_S = Z_L = 50 Ω ; T_{amb} = 25 °C				
		f = 1.5 GHz	-	34	-	dBm
		f = 1.8 GHz	-	34	-	dBm
		f = 2.4 GHz		33		dBm

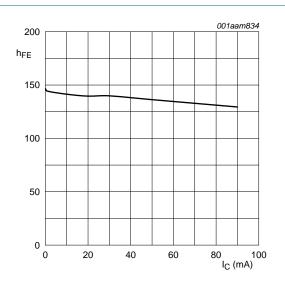
^[1] $G_{p(max)}$ is the maximum power gain, if K > 1. If K < 1 then $G_{p(max)} = MSG$.



 $T_{amb} = 25 \, ^{\circ}C.$

- (1) $I_B = 550 \mu A$
- (2) $I_B = 500 \mu A$
- (3) $I_B = 450 \mu A$
- (4) $I_B = 400 \mu A$
- (5) $I_B = 350 \mu A$
- (6) $I_B = 300 \mu A$
- (7) $I_B = 250 \mu A$
- (8) $I_B = 200 \mu A$ (9) $I_B = 150 \mu A$
- (10) $I_B = 100 \mu A$

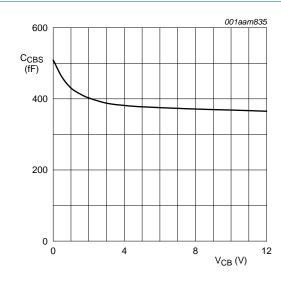
Fig 2. Collector current as a function of collector-emitter voltage; typical values



 $V_{CE} = 2 \text{ V}; T_{amb} = 25 \,^{\circ}\text{C}.$

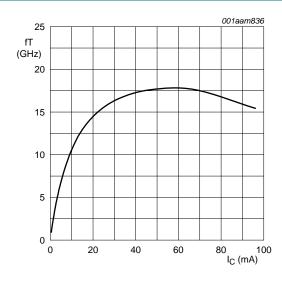
Fig 3. DC current gain as a function of collector current; typical values

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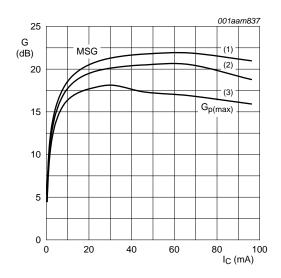
f = 1 MHz, $T_{amb} = 25$ °C.

Fig 4. Collector-base capacitance as a function of collector-base voltage; typical values



 $V_{CE} = 1 \text{ V; } f = 2 \text{ GHz; } T_{amb} = 25 \text{ }^{\circ}\text{C}.$

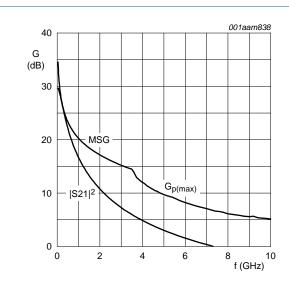
Fig 5. Transition frequency as a function of collector current; typical values



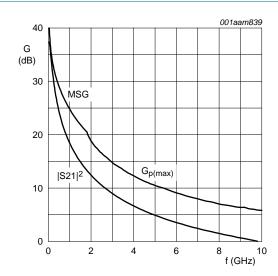
 $V_{CE} = 1 \text{ V; } T_{amb} = 25 \text{ }^{\circ}\text{C.}$

- (1) f = 1.5 GHz
- (2) f = 1.8 GHz
- (3) f = 2.4 GHz

Fig 6. Gain as a function of collector current; typical value



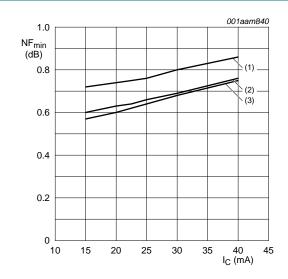
 V_{CE} = 1 V; I_{C} = 10 mA; T_{amb} = 25 °C.



 V_{CE} = 1 V; I_{C} = 60 mA; T_{amb} = 25 °C.

Fig 7. Gain as a function of frequency; typical values

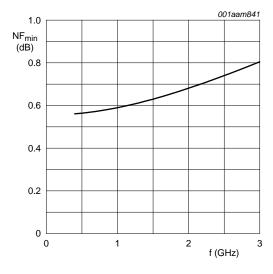




 V_{CE} = 2 V; T_{amb} = 25 °C.

- (1) f = 2.4 GHz
- (2) f = 1.8 GHz
- (3) f = 1.5 GHz

Fig 9. Minimum noise figure as a function of collector current; typical values



 V_{CE} = 2 V; I_{C} = 15 mA; T_{amb} = 25 °C.

Fig 10. Minimum noise figure as a function of frequency; typical values

Package outline

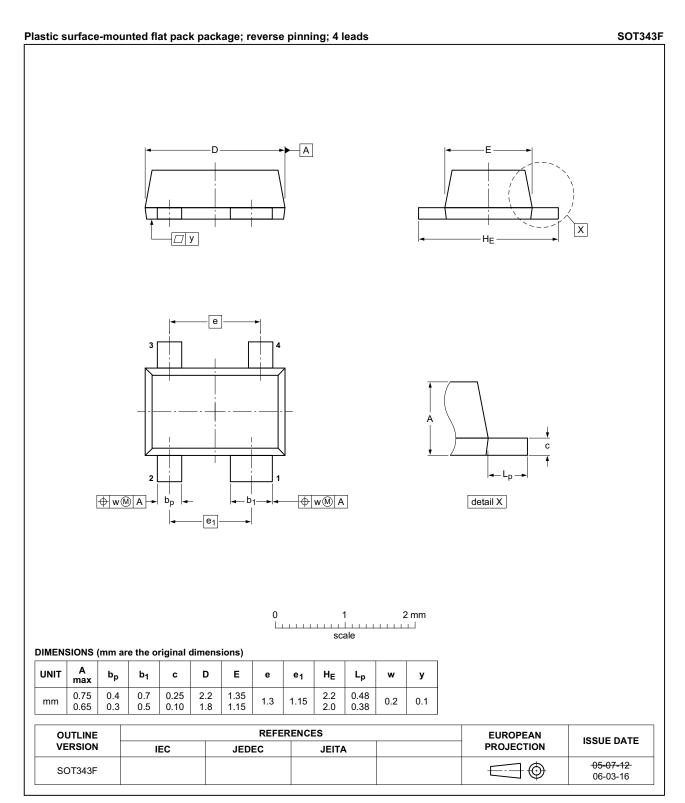


Fig 11. Package outline SOT343F

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9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 8. Abbreviations

Acronym	Description
DRO	Dielectric Resonator Oscillator
Ka	Kurtz above
LTE	Long Term Evolution
NPN	Negative-Positive-Negative
UMTS	Universal Mobile Telecommunications System

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BFU690F v.2	20140314	Product data sheet	-	BFU690F v.1		
Modifications:	Table 1 on pa	Table 1 on page 1: The value and conditions for Ptot have been updated.				
	 <u>Table 5 on page 2</u>: The value and conditions for P_{tot} have been updated. 					
	 <u>Table 6 on page 3</u>: The value and conditions for R_{th(j-sp)} have been updated. 					
	• Figure 1 on page 3: The graph has been updated.					
	• Section 9 on page 9: The ESD caution has been moved here from Section 1.1 on page 1.					
BFU690F v.1	20101216	Product data sheet	-	-		

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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